

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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PATENT
Supp.

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Application No.: 09/744,877 Filed: January 29, 2001

Filed: Januar Inventor(s):

Halimaoui, Aomar

Title: PROCESS FOR FORMING AN OXIDE LAYER OF

NON-UNIFORM

THICKNESS ON THE

SURFACE OF A SILICON

SUBSTRATE

Examiner:

Novacek, Christy L

Group/Art Unit: 2822

Atty. Dkt. No:

5310-03000

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

DATE OF DEPOSIT: 12-U-1

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail on the date indicated above and is addressed to:

Commissioner for Pateris

MCLU

SUPPLEMENTAL AMENDMENT

Commissioner for Patents Washington, D.C. 20231

Amendment

Sir:

Please amend the above-captioned application as follows:

In the Claims:

Please amend the claims as follows:

33. (Amended) A process for forming a semiconductor device comprising a plurality of MOS transistors at predetermined regions of a silicon substrate, comprising: